



PSMN7R8-100PSEQ Information



For Reference Only

Part Number PSMN7R8-100PSEQ Manufacturer Nexperia USA Inc.

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 100V SIL3

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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PSMN7R8-100PSEQ Specifications

Manufacturer Part Number PSMN7R8-100PSEQ Manufacturer Nexperia USA Inc. Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 100A (Tj) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ ImA Gate Charge (Qg) (Max) @ Vgs 128nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 7110pF @ 50V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 294W (Tc) Rds On (Max) @ Id, Vgs 7.8 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3		
CategoryDiscrete Semiconductor ProductsPackageTO-220-3Series-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C100A (Tj)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ ImAGate Charge (Qg) (Max) @ Vgs128nC @ 10VInput Capacitance (Ciss) (Max) @ Vds7110pF @ 50VVgs (Max)±20VFET Feature-Power Dissipation (Max)294W (Tc)Rds On (Max) @ Id, Vgs7.8 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220AB	Manufacturer Part Number	PSMN7R8-100PSEQ
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Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 100A (Tj) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 128nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 7.8 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Supplier Device Package Package / Case MOSFET (Metal Oxide) 100V 100V 100A (Tj) 4V @ 1mA 4V @ 1mA 128nC @ 10V 7110pF @ 50V ±20V FET F@ 50V **EQUATION** **EQUATION** **TO-220AB TO-220-3	Series	-
Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C100A (Tj)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 1mAGate Charge (Qg) (Max) @ Vgs128nC @ 10VInput Capacitance (Ciss) (Max) @ Vds7110pF @ 50VVgs (Max)±20VFET Feature-Power Dissipation (Max)294W (Tc)Rds On (Max) @ Id, Vgs7.8 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C 100A (Tj) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 1mA Gate Charge (Qg) (Max) @ Vgs 128nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 7110pF @ 50V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 294W (Tc) Rds On (Max) @ Id, Vgs 7.8 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220AB	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 4V @ 1mA Gate Charge (Qg) (Max) @ Vgs 128nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 7110pF @ 50V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 294W (Tc) Rds On (Max) @ Id, Vgs 7.8 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case TO-220AB	Drain to Source Voltage (Vdss)	100V
Vgs(th) (Max) @ Id 4V @ 1mA Gate Charge (Qg) (Max) @ Vgs 128nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 7110pF @ 50V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 294W (Tc) Rds On (Max) @ Id, Vgs 7.8 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Current - Continuous Drain (Id) @ 25°C	100A (Tj)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 7110pF @ 50V Vgs (Max) ±20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 7.8 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) E20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 7.8 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Vgs(th) (Max) @ Id	4V @ 1mA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)294W (Tc)Rds On (Max) @ Id, Vgs7.8 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Gate Charge (Qg) (Max) @ Vgs	128nC @ 10V
FET Feature - Power Dissipation (Max) 294W (Tc) Rds On (Max) @ Id, Vgs 7.8 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Input Capacitance (Ciss) (Max) @ Vds	7110pF @ 50V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 7.8 mOhm @ 25A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs7.8 mOhm @ 25A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Power Dissipation (Max)	294W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	7.8 mOhm @ 25A, 10V
Supplier Device Package TO-220AB Package / Case TO-220-3	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	TO-220AB
Report errors?	Package / Case	TO-220-3
100 post 511010 s		Report errors?

PSMN7R8-100PSEQ Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

PSMN7R8-100PSEQ Payment Methods



















PSMN7R8-100PSEQ Shipping Methods













If you have any question about PSMN7R8-100PSEQ, please do not hesitate to contact us!

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